

NTMFS4707N

Power MOSFET

30 V, 17 A, Single N-Channel,
SOIC-8 Flat Lead

Features

- Fast Switching Times
- Low Gate Charge
- Low $R_{DS(on)}$
- Low Inductance SOIC-8 Package
- These are Pb-Free Devices

Applications

- Notebooks, Graphics Cards
- DC-DC Converters
- Synchronous Rectification

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	30	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	10.2	A
		$T_A = 85^{\circ}\text{C}$		7.4	
	$t \leq 10\text{ s}$	$T_A = 25^{\circ}\text{C}$		17	
Power Dissipation (Note 1)	Steady State	$T_A = 25^{\circ}\text{C}$	P_D	2.3	W
	$t \leq 10\text{ s}$			6.25	
Continuous Drain Current (Note 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	6.9	A
		$T_A = 85^{\circ}\text{C}$		4.9	
Power Dissipation (Note 2)		$T_A = 25^{\circ}\text{C}$	P_D	1.0	W
Pulsed Drain Current	$t_p \leq 10\text{ }\mu\text{s}$		I_{DM}	51	A
Operating Junction and Storage Temperature			T_J , T_{STG}	-55 to 150	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	6.25	A
Single Pulse Drain-to-Source Avalanche Energy ($V_{DD} = 25\text{ V}$, $V_{GS} = 10\text{ V}$, $I_{PK} = 7.0\text{ A}$, $L = 10\text{ mH}$, $R_G = 25\text{ }\Omega$)			E_{AS}	245	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	55	$^\circ\text{C/W}$
Junction-to-Ambient – $t \leq 10\text{ s}$ (Note 1)	$R_{\theta JA}$	20	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	122.5	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

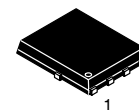
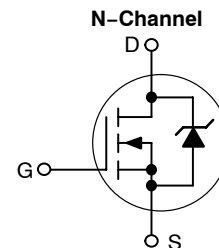
1. Surface-mounted on FR4 board using 1 in sq pad size
(Cu area = 1.127 in sq [1 oz] including traces).
2. Surface-mounted on FR4 board using the minimum recommended pad size
(Cu area = 0.412 in sq).



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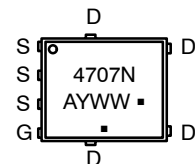
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$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
30 V	10 m Ω @ 10 V	17 A
	13.5 m Ω @ 4.5 V	



SOIC-8 FLAT LEAD
CASE 488AA
STYLE 1

MARKING DIAGRAM & PIN ASSIGNMENT



4707N = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTMFS4707NT1G	SOIC-8 FL (Pb-Free)	1500 / Tape & Reel
NTMFS4707NT3G	SOIC-8 FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTMFS4707N

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	30			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			6.5		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 24 V	T _J = 25°C		1.0	μA
			T _J = 125°C		50	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0		2.5	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			5.0		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 10 A		10	13	mΩ
		V _{GS} = 4.5 V, I _D = 8.0 A		13.5	17	
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 10 A		20		S

CHARGES, CAPACITANCES AND GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 24 V		735		pF
Output Capacitance	C _{OSS}			295		
Reverse Transfer Capacitance	C _{RSS}			80		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 15 V; I _D = 10 A		7.5	15	nC
Threshold Gate Charge	Q _{G(TH)}			1.1		
Gate-to-Source Charge	Q _{GS}			2.0		
Gate-to-Drain Charge	Q _{GD}			3.6		
Gate Resistance	R _G			2.4		Ω

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 10 V, V _{DD} = 15 V, I _D = 1.0 A, R _G = 3.0 Ω		6.0		ns
Rise Time	t _r			5.0		
Turn-Off Delay Time	t _{d(off)}			19		
Fall Time	t _f			11		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 6.25 A	T _J = 25°C		0.79	1.0	V
			T _J = 125°C		0.59		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 6.25 A		26			ns
Charge Time	t _a			14			
Discharge Time	t _b			12			
Reverse Recovery Charge	Q _{RR}			19			nC

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERIZATIONS

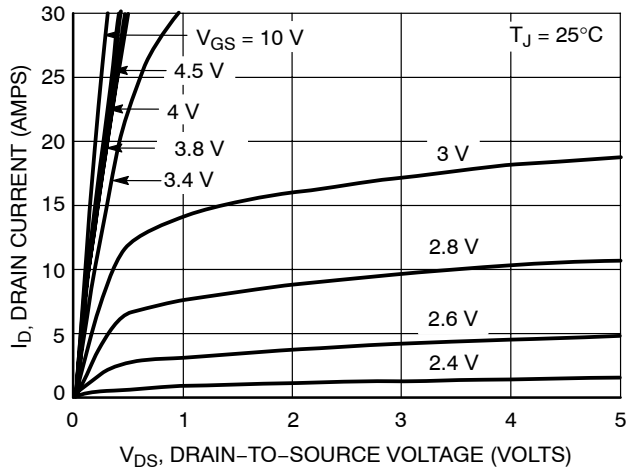


Figure 1. On-Region Characteristics

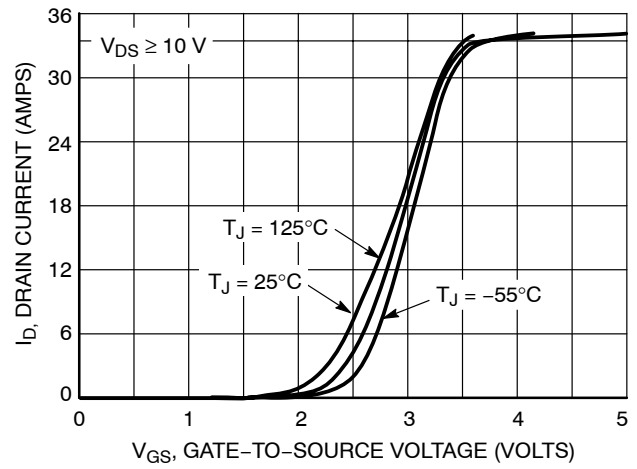


Figure 2. Transfer Characteristics

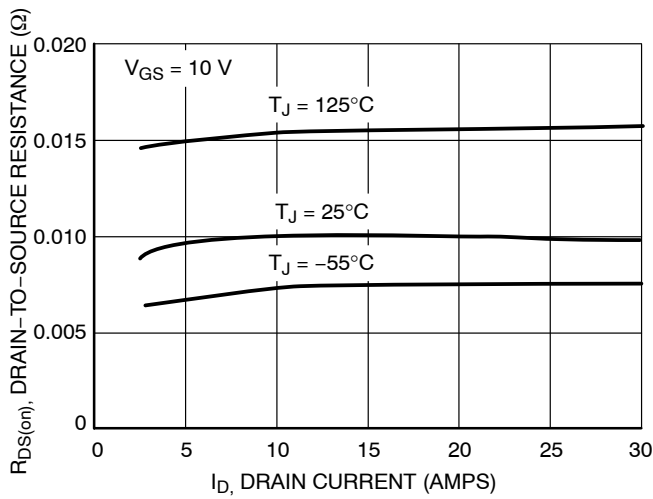


Figure 3. On-Resistance vs. Drain Current and Temperature

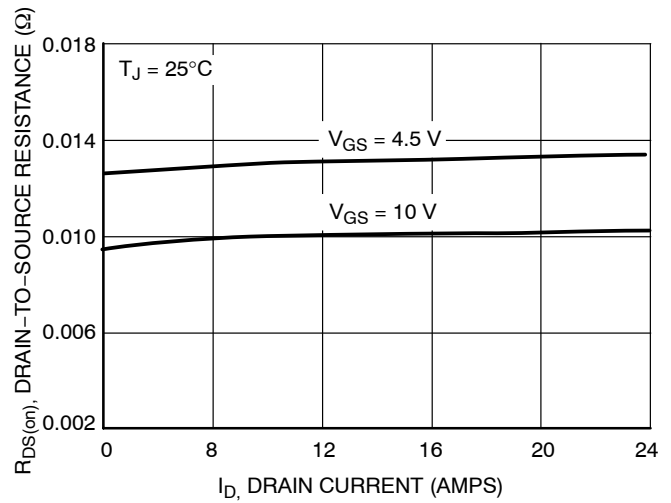


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

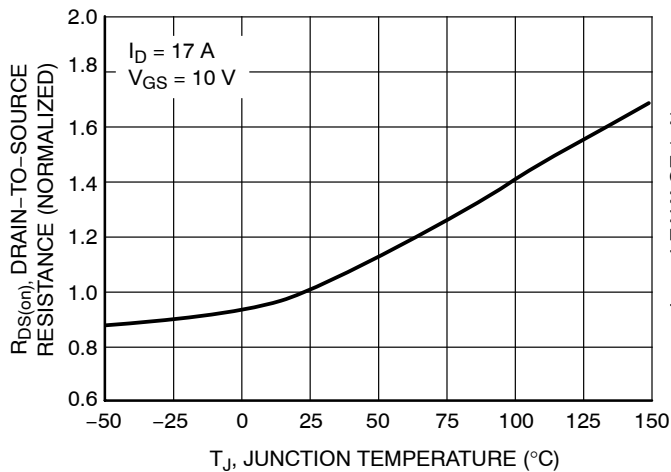


Figure 5. On-Resistance Variation with Temperature

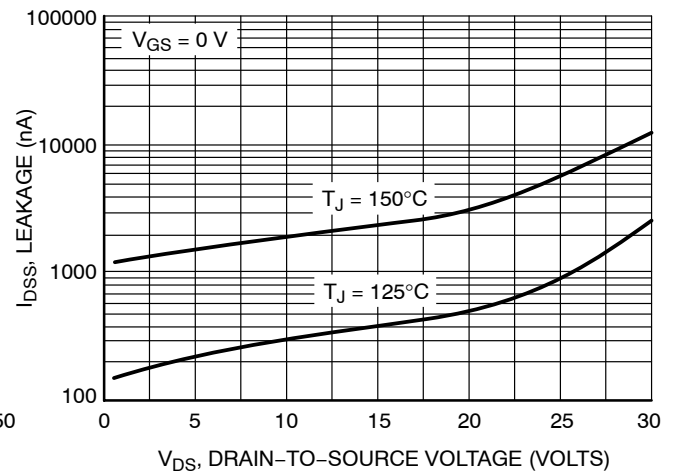
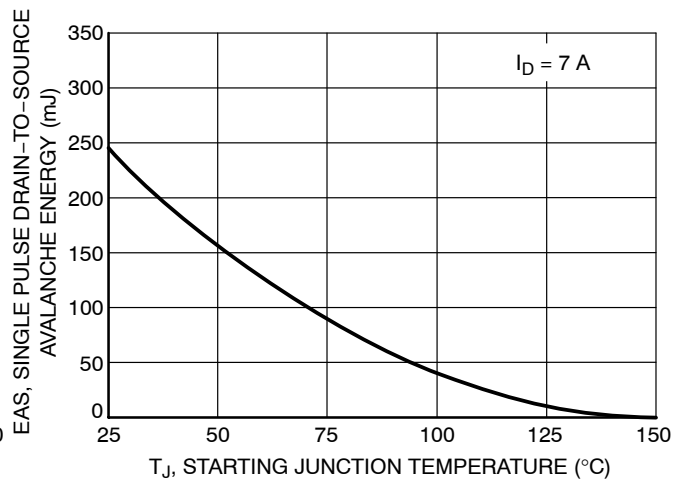
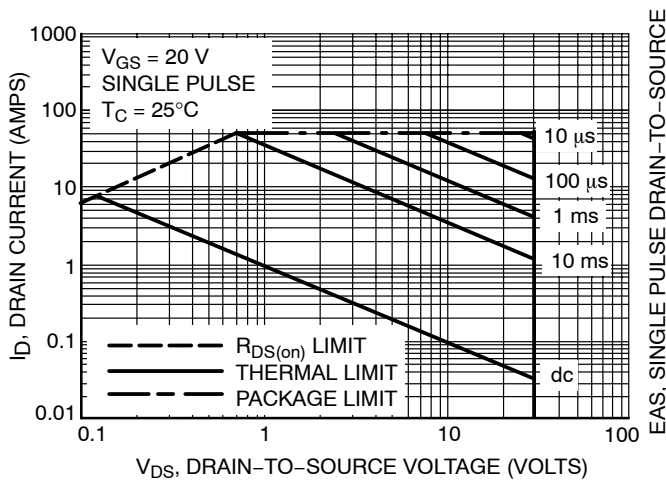
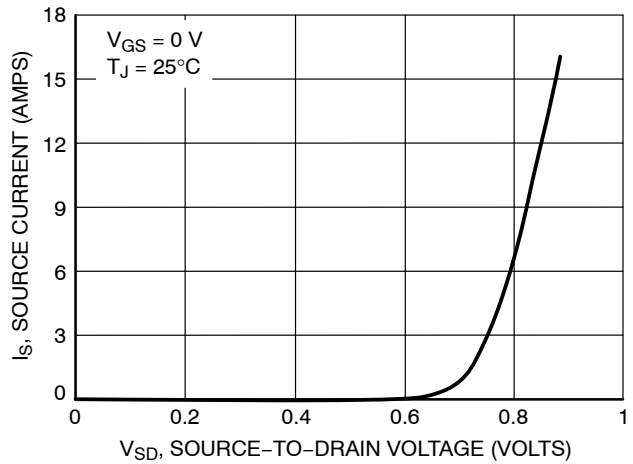
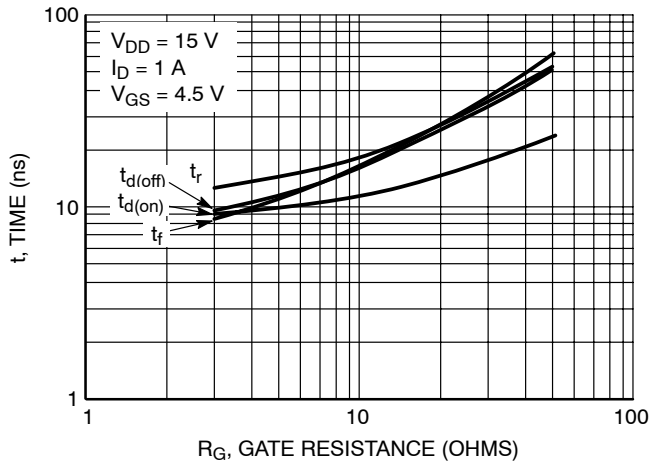
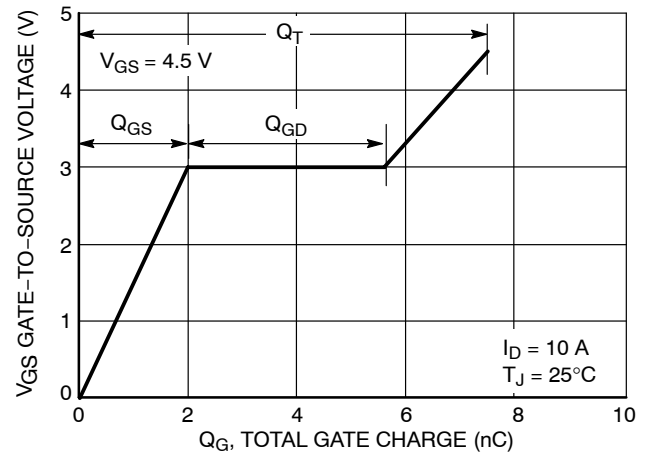
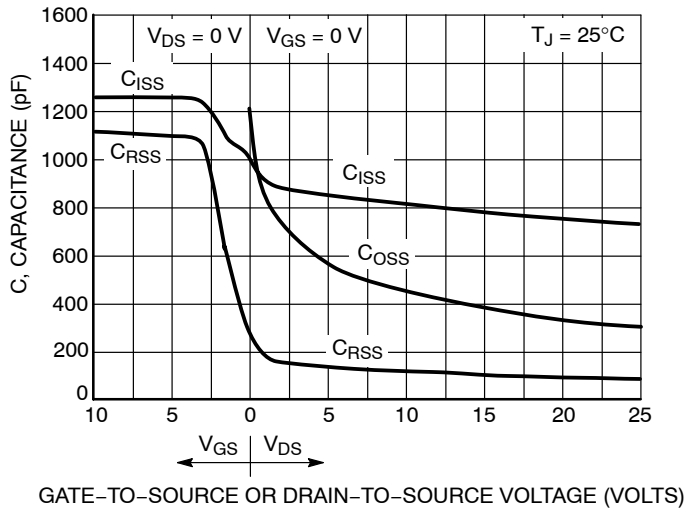


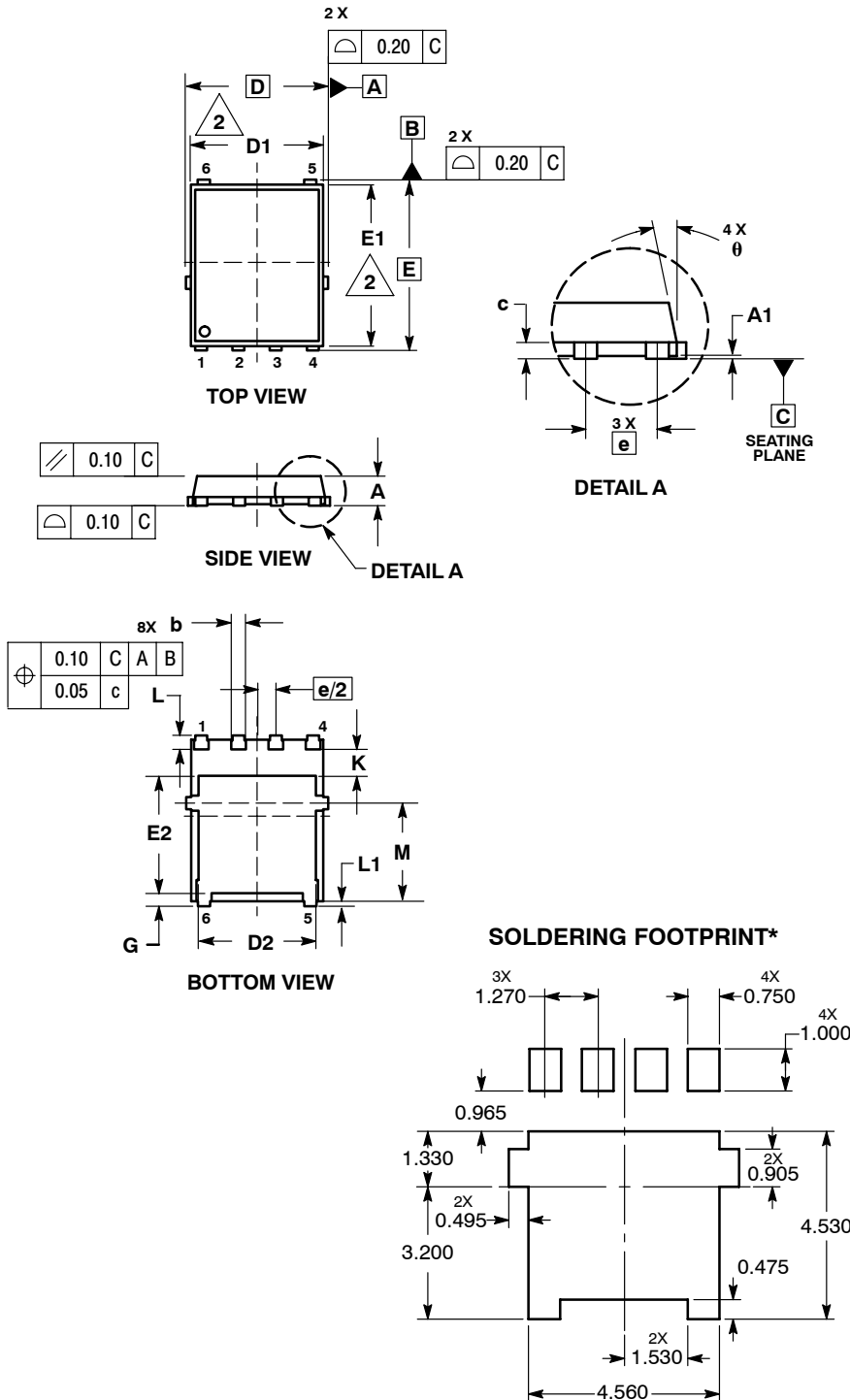
Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERIZATIONS



3. PACKAGE DIMENSIONS

DFN6 5*6*1 1.27 PITCH
(SO8 FL)
CASE 488AA-01
ISSUE B



NOTES:


1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.90	0.99	1.20
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.15 BSC		
D1	4.50	4.90	5.10
D2	3.50	---	4.22
E	6.15 BSC		
E1	5.50	5.80	6.10
E2	3.45	---	4.30
e	1.27 BSC		
G	0.51	0.61	0.71
K	0.51	---	---
L	0.51	0.61	0.71
L1	0.05	0.17	0.20
M	3.00	3.40	3.80
θ	0 °	---	12 °

STYLE 1:

- PIN 1. SOURCE
- SOURCE
- SOURCE
- GATE
- DRAIN
- DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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